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13. ABSTRACT (Maximum 200 words) The Ninth International Conference on Hot Carriers in Semiconductors (HCIS-9) was held July 31 - August 4, 1995 in Chicago, Illinois. It drew an international contingent of 170 scientist from 19 countries including the USA, the United Kingdom, Germany, Japan, the former Soviet Union, Italy and Austria. The research discussed at this conference advanced the state of the art in many areas, and it is expected to open new horizons in nonlinear transport studies, particularly in the areas of hot-electron and quantum transport. An attempt was made by the program committee to increase the number of presentations related directly to devices for this HCIS conference. Such works produced a rich discussion on a variety of transport effects.				
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Hot Carriers in Semiconductors

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**NINTH INTERNATIONAL CONFERENCE ON
HOT CARRIERS IN SEMICONDUCTORS**

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The *Ninth International Conference on Hot Carriers in Semiconductors* (HCIS-9) was held July 31 – August 4, 1995 in Chicago, Illinois. It drew an international contingent of 170 scientist from 19 countries including the USA, the United Kingdom, Germany, Japan, the former Soviet Union, Italy and Austria. The research discussed at this conference advanced the state of the art in many areas, and it is expected to open new horizons in nonlinear transport studies, particularly in the areas of hot-electrons and quantum transport.

Contributions to early HCIS conferences concentrated mainly on the basic physics of hot electron and hole transport in bulk semiconductors, mostly Ge, Si and GaAs. At later HCIS conferences, progress in the fabrication of new forms of semiconductor heterostructures grown by MBE and other techniques spawned contributions on transport effects in small and ultrasmall semiconductor structures such as tunneling, resonant tunneling, ballistic transport, and low-dimensional transport at later HCIS conferences. Advances in fabrication and theory were accompanied by experimental investigations using ever advancing techniques, such as femtosecond spectroscopy.

HCIS-9 continued the advancement of the state of art in many areas. Presentations addressed the latest issues in non-linear transport and fast electron dynamics in semiconductor materials and devices, and included both theoretical and experimental works. In addition, an attempt was made by the program committee to increase the number of presentations related directly to devices for this HCIS conference. Such works produced a rich discussion on a variety of transport effects. For example, one invited presentation on the the new quantum cascade laser by Federico Capasso (AT&T Bell Labs) alone raised issues of hot electron

effects, size quantization, and intersubband scattering. In our opinion, such results suggests that future conferences should further encourage reports on such device research.

In all there were 15 invited oral presentations, 60 contributed oral presentations and 105 poster presentations. The major areas addressed were hot carrier luminescence and femtosecond spectroscopy including measurement of carrier-phonon interactions in low-dimensional systems, Bloch oscillations and fast coherent processes in semiconductors including negative differential conductance in superlattices, hot carriers in nanostructures and low-dimensional systems including quantum transport and energy relaxation processes, high field transport and impact ionization including propagation of high-field domains and current instabilities, and hot electrons in devices including transport in quantum well lasers.

The conference proceedings are currently being prepared by Plenum Publishing Corporation. A copy will be sent as soon as available.